



浙江芯芯电子有限公司
ZHEJIANG XINXIN ELECTRICAL CO., LTD.

产品规格书

Specification of Products

产品名称：平板型

产品型号：KK2000A

浙江芯芯电子有限公司

ZHEJIANG XINXIN ELECTRICAL CO., LTD.

地址：浙江省缙云县壶镇镇浙江丽缙五金科技产业园苍山区块内

电话： 13857067071

邮编： 321404

E-mail:247145749@qq.com

<http://www.zjxxdz1.com>

拟制	审核	核准
丁国盛	李园利	麻伟阳

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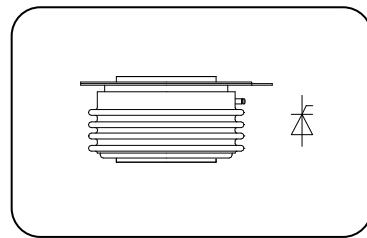
Features

- Interdigitated amplifying gates
- Fast turn-on and high dI/dt
- Low switching losses

Typical Applications

- Inductive heating
- Electronic welders
- Self-commutated inverters

$I_{T(AV)}$	2160A
V_{DRM}/V_{RRM}	1900~2500V
t_q	40~80μs
I_{TSM}	22.7 kA
I^2t	2576 10³A²S



SYMBOL	CHARACTERISTIC	TEST CONDITIONS	$T_j(^\circ C)$	VALUE			UNIT
				Min	Type	Max	
$I_{T(AV)}$	Mean on-state current	180° half sine wave 50Hz Double side cooled, $T_c=55^\circ C$ $T_c=85^\circ C$ old model	125			2160	A
						1450	
						2000	
V_{DRM} V_{RRM}	Repetitive peak off-state voltage Repetitive peak reverse voltage	$V_{DRM} \& V_{RRM}$, $tp=10ms$ $V_{DSM} \& V_{RSM}= V_{DRM} \& V_{RRM} + 100V$	125	1900		2500	V
I_{DRM} I_{RRM}	Repetitive peak current	$V_D=V_{DRM}$ $V_R=V_{RRM}$	125			160	mA
I_{TSM}	Surge on-state current	10ms half sine wave $V_R=0.6V_{RRM}$	125			22.7	kA
I^2t	I^2t for fusing coordination					2576	$A^2s \times 10^3$
V_{TO}	Threshold voltage		125			1.48	V
r_T	On-state slop resistance					0.23	$m\Omega$
V_{TM}	Peak on-state voltage	$I_{TM}=4000A$, $F=35kN$	125			2.40	V
dv/dt	Critical rate of rise of off-state voltage	$V_{DM}=0.67V_{DRM}$	125			500	$V/\mu s$
di/dt	Critical rate of rise of on-state current	$V_{DM}= 67\%V_{DRM}$ to 3000A Gate pulse $t_r \leq 0.5\mu s$ $I_{GM}=1.5A$	125			1200	$A/\mu s$
Q_{fr}	Recovery charge	$I_{TM}=2000A$, $tp=2000\mu s$, $di/dt=-60A/\mu s$, $V_R=50V$	125		1400		μC
t_q	Circuit commutated turn-off time	$I_{TM}=1700A$, $tp=1000\mu s$, $V_R=50V$ $dv/dt=30V/\mu s$, $di/dt=-20A/\mu s$	125	40		80	μs
I_{GT}	Gate trigger current	$V_A=12V$, $I_A=1A$	25			450	mA
V_{GT}	Gate trigger voltage			0.9		4.5	V
I_H	Holding current			20		1000	mA
V_{GD}	Non-trigger gate voltage	$V_{DM}=67\%V_{DRM}$	125	0.3			V
$R_{th(j-c)}$	Thermal resistance Junction to case	At 180° sine double side cooled Clamping force 35kN				0.012	$^\circ C / W$
$R_{th(c-h)}$	Thermal resistance case to heat sink					0.003	
F_m	Mounting force			30		40	kN
T_{stg}	Stored temperature			-40		140	°C
W_t	Weight				880		g
Outline		KT60cT70					

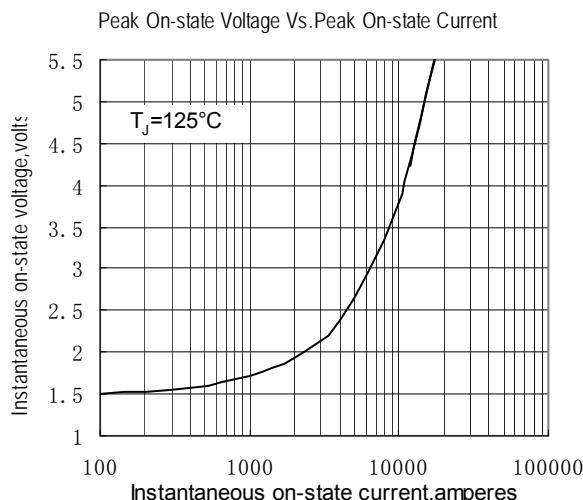


Fig.1

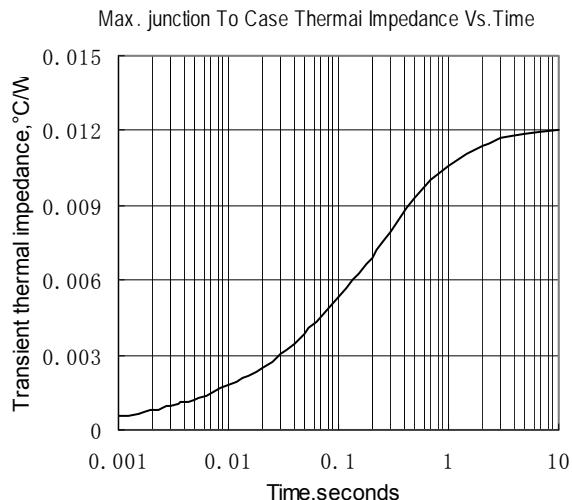


Fig.2

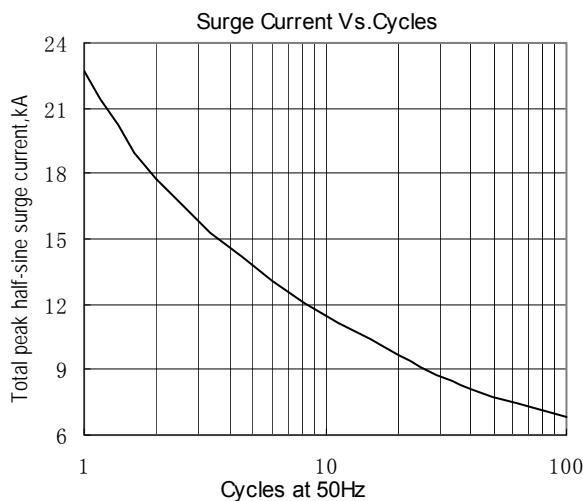


Fig.3

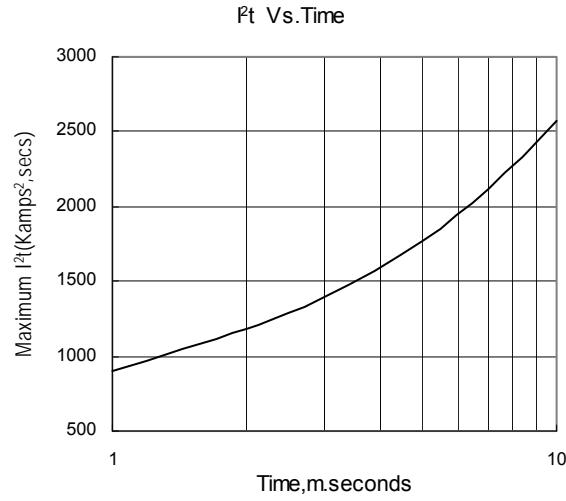


Fig.4

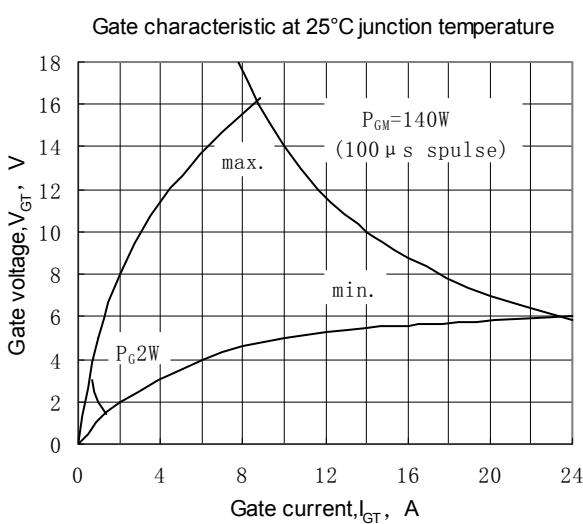


Fig.5

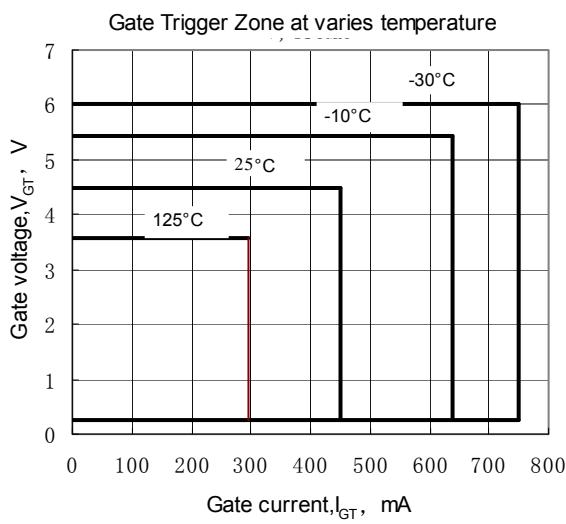


Fig.6

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Outline:

